NSN 5962-01-162-4681

Memory Microcircuit - Page 1 of 2



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Body Length: 1.220 inches Body Width: 0.600 inches Body Height: 0.005 inches Body Indight: 0.005 inches Body Height: Body Height: 0.005 inches Body Height:	
0.000 inches Body Height: 0.005 inches Maximur Power Dissipation Rating: 00.00 milliwatts Operating Tempurature Range: 0.50.0/+102.00 degrees celsius Storage Tempurature Range: 0.60.0/+102.00 degrees celsius Portage Tempurature Range: 0.60.0/+102.00 degrees celsius End Application: 520-0/+102.0321 digital message Features Provided: Static operation and hermetically sealed and programmable and expandable and 3-state output Inclosure Material: Complementary-metal oxide-semiconductor logic Industrine Output Logic Form: Complementary-metal oxide-semiconductor logic Input Circuit Pattern: 12 logit Stolar power source Notage Rating And Type Per Characteristic: 13 logit power source Voltage Rating And Type Per Characteristic: 15 volts power source Time Rating Per Characteristic: 16 source source source sources propagation delay time, low to high level output and 850 00 nanoseconds propagation delay time, low to high level output and 850 00 nanoseconds propagation delay time, low to high level sources delay time, low to high level sources delay time, low	
0.000 inches Body Height: 0.005 inches Maximu Power Dissipation Rating: 00.00 milliwatts Operating Tempurature Range: 0.50./+125.0 degrees celsius Storage Tempurature Range: 0.60./+150.0 degrees celsius End Application: 0.60./+102.0 320 digital message Features Provided: Static operation and hermetically sealed and programmable and expandable and 3-state output Inclosure Material: Corsamic Dutput Logic Form: Complementary-metal oxide-semiconductor logic Input Circuit Pattern: 12 logit 12 logit Stolar per Source Stolar per Source Terminal Surface Treatment: Stolar Stolar per Characteristic: 12 logit Time Rating And Type Per Characteristic: 15 voltis power source Time Rating Per Characteristic: 15 voltis power source Time Rating Per Characteristic: Stolar prove Source spreagation delay time, low to high level output and 85.00 nanoseconds propagation delay time, low to high level output and 85.00 nanoseconds propagation delay time, low to high level	
0.095 inches Aximum Power Dissipation Rating: 50.01 milliwatts Operating Tempurature Range: -55.0/125.0 degrees celsius Storage Tempurature Range: -55.0/125.0 degrees celsius Extra Application: 520-01-102-3921 digital message Features Provided: Static operation and hermetically sealed and programmable and expandable and 3-state output Inclosure Material: Ceramic Inclosure Material: Complementary-metal oxide-semiconductor logic Input Circuit Pattern: 12 input Terminal Surface Treatment: Solder Voltage Rating And Type Per Characteristic: 15.5 olts prover source Time Rating Per Characteristic: 15.0 solts prover source State output Index per Surface	
0.095 inches Aximum Power Dissipation Rating: 50.01 milliwatts Operating Tempurature Range: -55.04/125.0 degrees celsius Storage Tempurature Range: -55.04/125.0 degrees celsius Extra Application: -66.04/150.0 degrees celsius Extra Application: 5820-01-102-3921 digital message Features Provided: Static operation and hermetically sealed and programmable and expandable and 3-state output Inclosure Material: Ceramic Inclosure Material: Ceramic Inclosure Configuration: Dual-in-line Output Logic Form: Complementary-metal oxide-semiconductor logic Input Circuit Pattern: 12 input Terminal Surface Treatment: Solder Vottage Rating And Type Per Characteristic: 15.5 volts power soure Extra Surface Treatment: Solots nonseeconds propagation delay time, low to high level output and 850.00 nanoseconds propagation delay time, high to low to toput Kenory Device Type: Rom	
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output Memory Device Type: Rom Memory Capacity:	stic:
Memory Device Type: Rom Memory Capacity:	agation delay time, low to high level output and 850.00 nanoseconds propagation delay time, high to low level
Rom Memory Capacity:	
Memory Capacity:	
Unknown	
Terminal Type And Quantity:	ity:
24 printed circuit	
Shelf Life:	
N/a	
Unit Of Measure:	

Yes - demil/mli

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